Mirhasan Seyitsoy

List of Publications by Year
in descending order

40 papers	365 citations	759233 12 h-index	888059 17 g-index
41 all docs	41 docs citations	41 times ranked	147 citing authors

#	Article	IF	Citations
1	Negative thermal expansion due to negative area compressibility in TlGaSe2 semiconductor with layered crystalline structure. Journal of Applied Physics, 2010, 108, 063540.	2.5	37
2	The effect of impurities on the phase transitions in the ferroelectric semiconductors TlInS2and TlGaSe2. Journal of Physics Condensed Matter, 2005, 17, 1985-1993.	1.8	28
3	The effect of thermal annealing on impurity states in ferroelectric- semiconductor TlGaSe2within the incommensurate phase. Semiconductor Science and Technology, 2006, 21, 171-174.	2.0	23
4	Electret states and current oscillations in the ferroelectric semiconductor TlGaSe2. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 3781-3787.	1.8	18
5	Dielectric spectroscopy and nonequilibrium phase transitions in TlGaSe2layered crystals. Semiconductor Science and Technology, 2007, 22, 843-850.	2.0	18
6	Mechanisms of current flow in p-TlGaSe2single crystals. Semiconductor Science and Technology, 2006, 21, 1633-1638.	2.0	15
7	Origin of structural instability in TlInS_{2(1â^’<i>x</i>)}Se_{2<i>x</i>}solid solutions. Physica Scripta, 2011, 84, 015601.	2.5	14
8	Effect of illumination on negative linear expansion of TlGaSe2 layered crystals. Journal of Physics and Chemistry of Solids, 2008, 69, 2544-2547.	4.0	13
9	Electric field instabilities in TlGaSe2 crystals. Solid State Sciences, 2008, 10, 1666-1670.	3.2	13
10	Characterization of deep level defects and thermally stimulated depolarization phenomena in La-doped TlInS2 layered semiconductor. Journal of Applied Physics, 2015, 117, .	2.5	13
11	Identification of intrinsic deep level defects responsible for electret behavior in TlGaSe2 layered semiconductor. Physica B: Condensed Matter, 2016, 483, 82-89.	2.7	13
12	Thermal expansion and memory effect in the ferroelectric-semiconductor TlGaSe2. Journal of Applied Physics, 2009, 106, 023532.	2.5	12
13	Memory effect and new polarized state in the incommensurate phase of TlGaSe2 ferroelectric â€" semiconductor. Journal of Applied Physics, 2011, 110, 013529.	2.5	11
14	Imprint electric field controlled electronic transport in TlGaSe2 crystals. Journal of Applied Physics, 2013, 114, 093706.	2.5	11
15	Origin of the optical absorption of TlGaSe₂ layered semiconductor in the visible range. Semiconductor Science and Technology, 2018, 33, 075019.	2.0	10
16	Preparation, crystal structure, and electrical properties of thallium monosulfide in the vicinity of high-temperature phase transitions. Physics of the Solid State, 2006, 48, 2322-2327.	0.6	9
17	Effect of electric field on negative linear expansion of ferroelectric-semiconductor TlGaSe2. Journal of Applied Physics, 2009, 106, 063529.	2.5	9
18	Charge disproportionation in TlGaSe2 crystals detected by dielectric spectroscopy. Journal of Applied Physics, 2010, 108, 074114.	2.5	8

#	Article	IF	Citations
19	Phase transition sensitive to interlayer defects in layered semiconductor TlGaSe2. Solid State Sciences, 2012, 14, 311-316.	3.2	8
20	Photoelectric activity of defects in La-doped layered TlInS2 crystals. Low Temperature Physics, 2014, 40, 830-836.	0.6	7
21	Temperature-dependent polarity reversal in Au/TlGaSe2 Schottky junctions. Journal of Applied Physics, 2009, 105, 043710.	2.5	6
22	Enhancing the photoresponse of a TlGaSe₂semiconductor for ultraviolet detection applications. Physica Scripta, 2015, 90, 015805.	2.5	6
23	Effect of deep native defects on ultrasound propagation in TlInS2 layered crystal. Physica B: Condensed Matter, 2016, 497, 86-92.	2.7	6
24	The Role of Electronic Subsystem in the Negative Thermal Expansion of Ferroelectricâ€"Semiconductor TlGaSe2. Japanese Journal of Applied Physics, 2011, 50, 05FD06.	1.5	5
25	Polarization switching in undoped and La-doped TlInS2 ferroelectric-semiconductors. Physica B: Condensed Matter, 2017, 526, 45-53.	2.7	5
26	Diode Polarization and Resistive Switching in Metal/TlGaSe2 Semiconductor/Metal Devices. Semiconductors, 2018, 52, 2007-2016.	0.5	5
27	Mott barrier behavior of metalâ€"TlGaSe₂ layered semiconductor junction. Semiconductor Science and Technology, 2020, 35, 125010.	2.0	5
28	Activated impurity states in the incommensurate phase of ferroelectric semiconductor TlInS2. Journal of Applied Physics, 2010, 108, 024111.	2.5	4
29	Photoinduced Current Transient Spectroscopy of TlInS2Layered Crystals Doped with Er, B, and Tb Impurities. Japanese Journal of Applied Physics, 2011, 50, 05FC08.	1.5	4
30	Field induced rectification and memristive behavior of TlGaSe2 layered semiconductor. Applied Physics Letters, 2014, 105, 152106.	3.3	4
31	Preparation, structure analysis and dielectric characteristics of the novel ferroelectric ceramics (1â^') Tj ETQq1 1 0.784314 rgBT /Over structure. Journal of Alloys and Compounds, 2017, 711, 169-183.	5.5	4
32	Preillumination â€" Induced change of electronic transport properties of TlGaSe2 semiconductor. Solid State Sciences, 2014, 33, 49-52.	3.2	3
33	Identification of Mn dopant in the structure of TlInS₂ layered semiconductor. Materials Research Express, 2019, 6, 056110.	1.6	3
34	Magnetic resonance and magnetization studies of Fe implanted TlInS₂ and TlGaSe₂ crystals. Materials Research Express, 2019, 6, 076109.	1.6	3
35	A Study of Thermoelectric Performance of TlGaSe₂ Layered Dichalcogenides from Firstâ€Principles Calculations: Vacancy Defects Modeling and Engineering. Physica Status Solidi (B): Basic Research, 2022, 259, 2100409.	1.5	3
36	Synthesis and magnetic characterizations of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si7.svg"><mml:mrow><mml:mi mathvariant="normal">T</mml:mi><mml:mi mathvariant="normal">l</mml:mi><mml:msub><mml:mrow><mml:mi mathvariant="normal">I</mml:mi><mml:mi mathvariant="normal">n</mml:mi></mml:mrow><mml:mrow><mml:mn>1</mml:mn><mml:mo>-</mml:mo><mml:mi>x</mml:mi></mr	2.3	3

#	Article	IF	Citations
37	Investigation of Basic Optical Properties of Tissue Phantoms Under 635 nm Low-Level Laser Irradiation. , 2020, , .		2
38	Charged Defects as an Origin of the Memory Effect in Incommensurate Phase of TlInS2Ferroelectricâ€“Semiconductors. Japanese Journal of Applied Physics, 2011, 50, 05FD07.	1.5	2
39	Influence of native structural defects activated by illumination and under the memory effect conditions on ultrasonic wave propagation in TlInS₂ ferroelectricâ€“semiconductor with incommensurate phase. Materials Research Express, 2019, 6, 085914.	1.6	1
40	Synthesis, Powder Xâ€Ray Diffraction, and Ab Initio Study of TlInSe 2 : Analysis of Its Thermoelectric Properties. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800835.	1.8	1